

**Features:**

- n Isolated mounting base 3000V~
- n Solder joint technology with increased power cycling capability
- n Space and weight saving

**Typical Applications**

- n AC/DC Motor drives
- n Various rectifiers
- n DC supply for PWM inverter

| $V_{DRM}$ ,<br>$V_{RRM}$ | Type & Outline  |                  |
|--------------------------|-----------------|------------------|
|                          | 800V            | MFC135-08-229H3  |
| 1000V                    | MFC135-10-229H3 | MFC135-10-229H3B |
| 1200V                    | MFC135-12-229H3 | MFC135-12-229H3B |
| 1400V                    | MFC135-14-229H3 | MFC135-14-229H3B |
| 1600V                    | MFC135-16-229H3 | MFC135-16-229H3B |
| 1800V                    | MFC135-18-229H3 | MFC135-18-229H3B |

| SYMBOL                 | CHARACTERISTIC                             | TEST CONDITIONS  | $T_j(^{\circ}\text{C})$ | VALUE |      |      | UNIT                           |
|------------------------|--|--|-------------------------|-------|------|------|--------------------------------|
|                        |  |  |                         | Min   | Type | Max  |                                |
| $I_{T(AV)}$            | Mean on-state current                      | 180° half sine wave 50Hz<br>Single side cooled, $T_c=85^{\circ}\text{C}$ | 125                     |       |      | 135  | A                              |
| $I_{T(RMS)}$           | RMS on-state current                       |  | 125                     |       |      | 212  | A                              |
| $I_{DRM}$<br>$I_{RRM}$ | Repetitive peak current                    | at $V_{DRM}$<br>at $V_{RRM}$   | 125                     |       |      | 35   | mA                             |
| $I_{TSM}$              | Surge on-state current                     | 10ms half sine wave<br>$V_R=60\%V_{RRM}$                                 | 125                     |       |      | 3.5  | kA                             |
| $I^2t$                 | $I^2t$ for fusing coordination             |  |                         |       |      | 61.3 | $\text{A}^2\text{s}\cdot 10^3$ |
| $V_{TO}$               | Threshold voltage                          |  | 125                     |       |      | 0.95 | V                              |
| $r_T$                  | On-state slope resistance                  |  |                         |       |      | 1.50 | $\text{m}\Omega$               |
| $V_{TM}$               | Peak on-state voltage                      | $I_{TM}=410\text{A}$   | 25                      |       |      | 1.80 | V                              |
| $dv/dt$                | Critical rate of rise of off-state voltage | $V_{DM}=67\%V_{DRM}$   | 125                     |       |      | 1000 | $\text{V}/\mu\text{s}$         |
| $di/dt$                | Critical rate of rise of on-state current  | Gate source 1.5A<br>$t_r \leq 0.5\mu\text{s}$ Repetitive                 | 125                     |       |      | 200  | $\text{A}/\mu\text{s}$         |
| $I_{GT}$               | Gate trigger current                       | $V_A=12\text{V}$ , $I_A=1\text{A}$                                       | 25                      | 30    |      | 200  | mA                             |
| $V_{GT}$               | Gate trigger voltage                       |  |                         | 0.6   |      | 2.5  | V                              |
| $I_H$                  | Holding current                            |  |                         | 10    |      | 250  | mA                             |
| $I_L$                  | Latching current                           |  |                         |       |      | 1000 | mA                             |
| $V_{GD}$               | Non-trigger gate voltage                   | $V_{DM}=67\%V_{DRM}$   | 125                     |       |      | 0.2  | V                              |
| $R_{th(j-c)}$          | Thermal resistance<br>Junction to case     | Single side cooled per chip  |                         |       |      | 0.18 | $^{\circ}\text{C}/\text{W}$    |
| $R_{th(c-h)}$          | Thermal resistance<br>case to heatsink     | Single side cooled per chip  |                         |       |      | 0.08 | $^{\circ}\text{C}/\text{W}$    |
| $V_{iso}$              | Isolation voltage                          | 50Hz, R.M.S, $t=1\text{min}$ , $I_{iso}:1\text{mA(MAX)}$                 |                         | 3000  |      |      | V                              |
| $F_m$                  | Terminal connection torque(M6)             |  |                         | 4.5   |      | 6.0  | N·m                            |
|                        | Mounting torque(M6)                        |  |                         | 4.5   |      | 6.0  | N·m                            |
| $T_{vj}$               | Junction temperature                       |  |                         | -40   |      | 125  | $^{\circ}\text{C}$             |
| $T_{stg}$              | Stored temperature                         |  |                         | -40   |      | 125  | $^{\circ}\text{C}$             |
| $W_t$                  | Weight                                     |  |                         |       | 165  |      | g                              |
| <b>Outline</b>         | 229H3/229H3B                               |  |                         |       |      |      |                                |

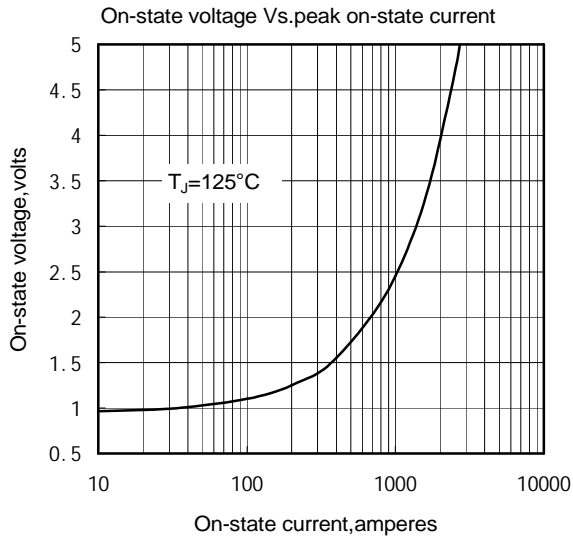


Fig1

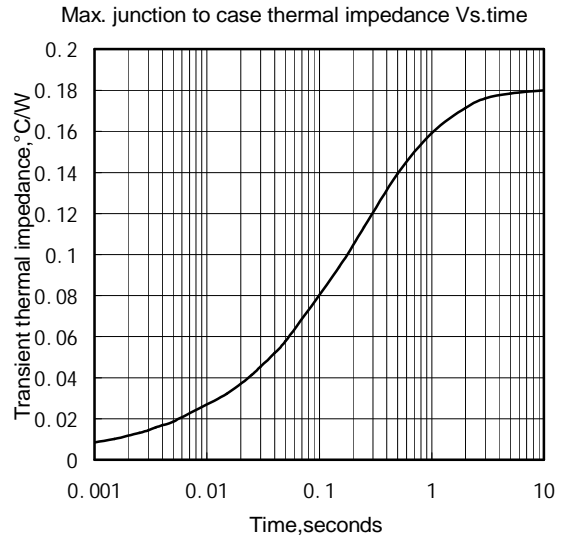


Fig2

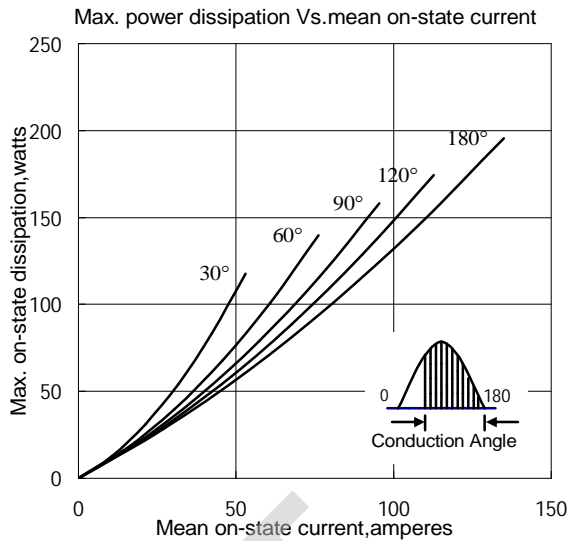


Fig3

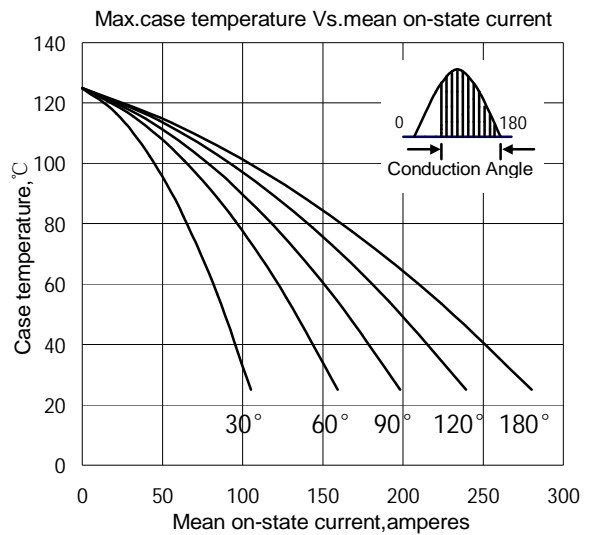


Fig4

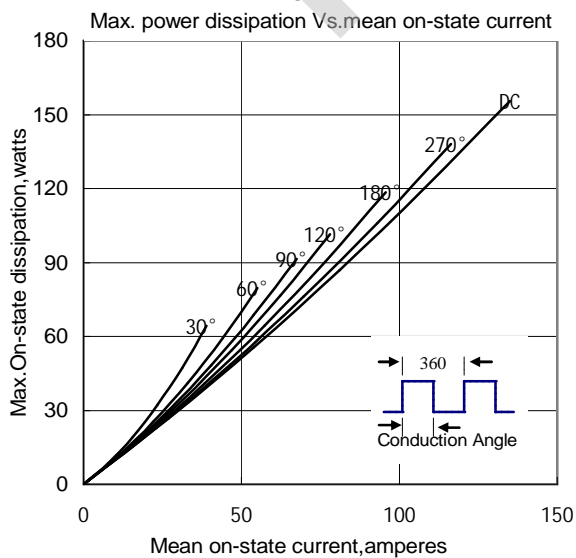


Fig5

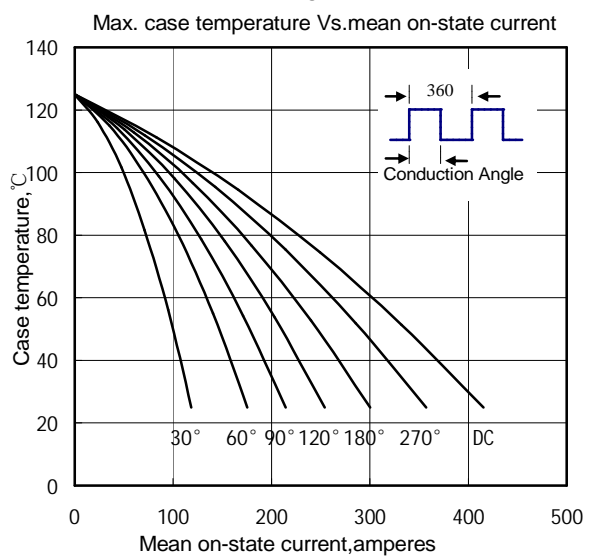


Fig6

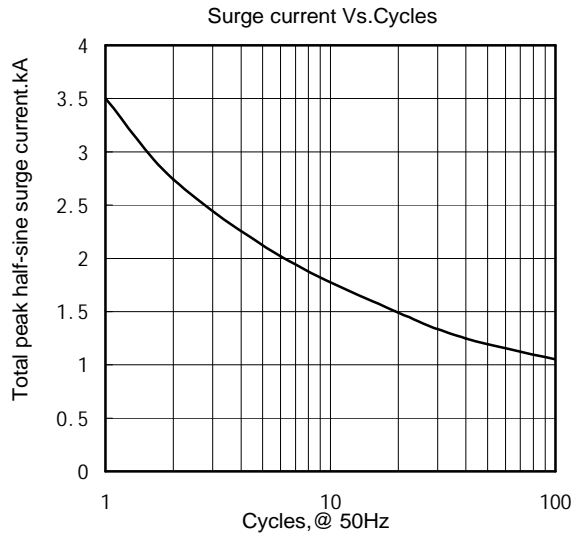


Fig 7

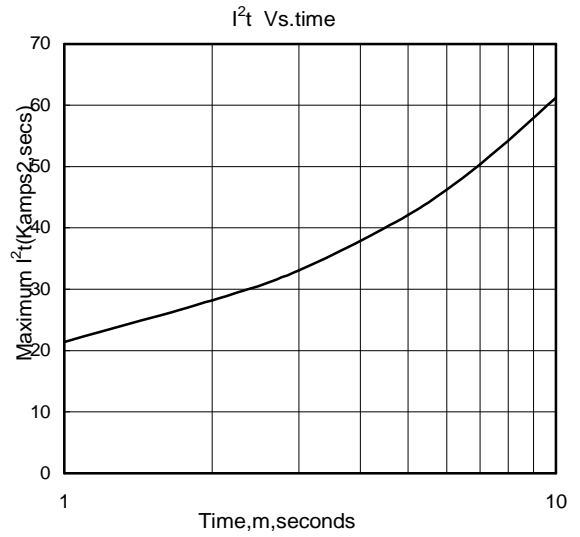


Fig 8

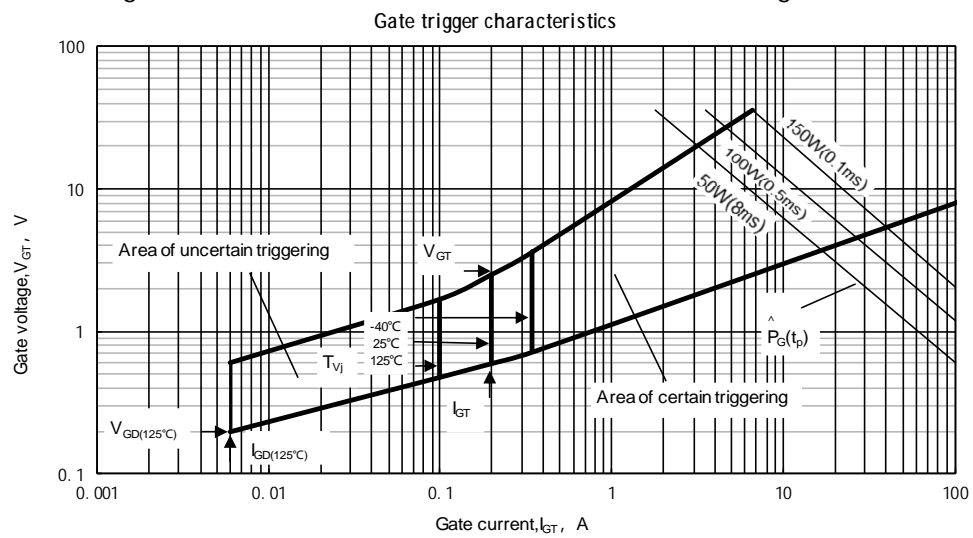
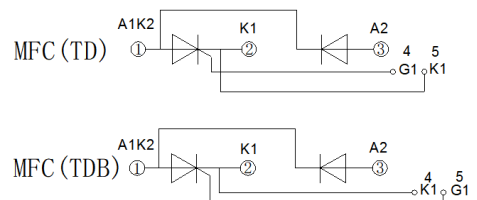
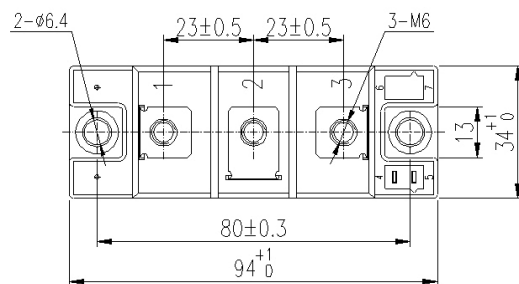
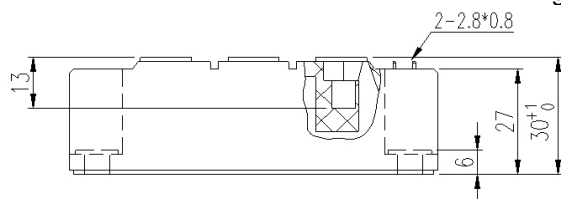


Fig.9

Outline:



Unmarked dimensional tolerance:  $\pm 0.5$ mm

TECHSEM reserves the right to change specifications without notice.